Octal D Flip-Flop with Common Clock and Reset with LSTTL-Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT273A may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs. The HCT273A is identical in pinout to the LS273.

This device consists of eight D flip-flops with common Clock and Reset inputs. Each flip-flop is loaded with a low-to-high transition of the Clock input. Reset is asynchronous and active low.

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 284 FETs or 71 Equivalent Gates
- These devices are available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.

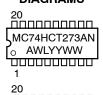


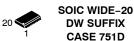
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A = Assembly Location

WL = Wafer Lot

YY = Year

WW = Work Week

PIN ASSIGNMENT

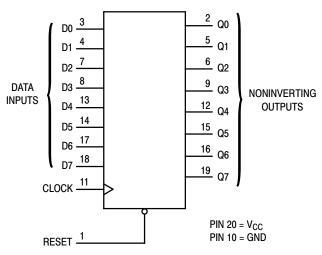
			_
RESET [1●	20] v _{cc}
Q0 [2	19] Q7
D0 [3	18] D7
D1 [4	17	D6
Q1 [5	16	□ Q6
Q2 [6	15	Q5
D2 [7	14] D5
D3 [8	13] D4
Q3 [9	12] Q4
GND [10	11	СГОСК

ORDERING INFORMATION

Device	Package	Shipping
MC74HCT273AN	PDIP-20	1440 / Box
MC74HCT273ADW	SOIC-WIDE	38 / Rail
MC74HCT273ADWR2	SOIC-WIDE	1000 / Reel

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LOGIC DIAGRAM



FUNCTION TABLE

	nputs	Output	
Reset	Clock	D	Q
L	Х	Х	L
Н		Н	Н
Н		L	L
Н	L	X	No Change
Н	~	Х	No Change

X = Don't Care

Z = High Impedance

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	$-$ 0.5 to V_{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	±[2 0	mA
I _{out}	DC Output Current, per Pin	±[2 5	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±[5 0	mA
P_{D}	Power Dissipation in Still Air Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or Plastic DIP)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	0	500	ns

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V_{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $\left I_{out}\right $ \leq 20 μA	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 4.0 \text{ mA}$	4.5	3.98	3.84	3.7	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 4.0 \text{ mA}$	4.5	0.26	0.33	0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	±[0.1	±[1.0	± <u>1</u> 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4.0	40	160	μΑ
ΔI_{CC}	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs		≥ -55°C	25°C to	125°C	
	Carrotte	$I_{\text{out}} = 0 \mu\text{A}$	5.5	2.9	2	.4	mA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (V_{CC} = $5.0 \text{ V} \pm 10\%$, C_L = 50 pF, Input t_r = t_f = 6.0 ns)

			Gu	aranteed Li	mit	
Symbol	Parameter	Fig.	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle)	1, 4	30	24	20	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q	1, 4	25	28	35	ns
t _{PHL}	Maximum Propagation Delay, Reset to Q	2, 4	25	28	35	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output	1, 5	18	20	22	ns

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

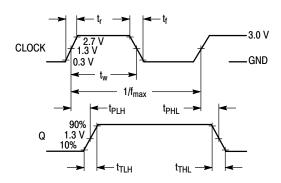
		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Gate)*	30	pF

^{*}Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (V_{CC} = 5.0 V \pm 10%, C_L = 50 pF, Input t_r = t_f = 6.0 ns)

			Guaranteed Limit						
			– 55 to	25°C	25°C ≤ 85°C		≤ 85°C ≤ 125°C		
Symbol	Parameter	Fig.	Min	Max	Min	Max	Min	Max	Unit
t _{su}	Minimum Setup Time, Data to Clock	3	10		12		15		ns
t _h	Minimum Hold Time, Clock to Data	3	3.0		3.0		3.0		ns
t _{rec}	Minimum Recovery Time, Set or Reset Inactive to Clock	2	5.0		5.0		5.0		ns
t _w	Minimum Pulse Width, Clock	1	12		15		18		ns
t _w	Minimum Pulse Width, Set or Reset	2	12		15		18		ns
t _r , t _f	Maximum Input Rise and Fall Times	1		500		500		500	ns

SWITCHING WAVEFORMS



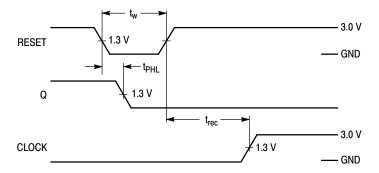
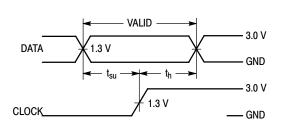
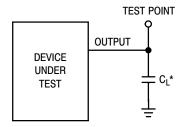


Figure 1.

Figure 2.



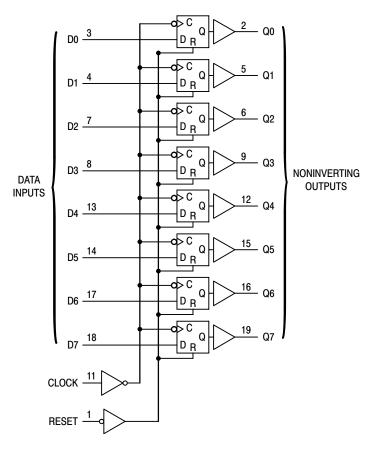




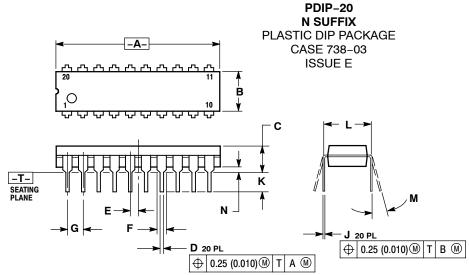
*Includes all probe and jig capacitance

Figure 4. Test Circuit

EXPANDED LOGIC DIAGRAM



PACKAGE DIMENSIONS



NOTES:

- IOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

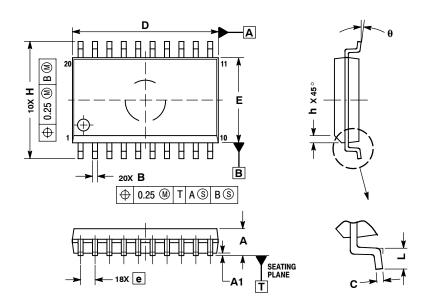
 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
С	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
Е	0.050 BSC		1.27 BSC		
т	0.050	0.070	1.27	1.77	
G	0.100	0.100 BSC		BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
Г	0.300 BSC		7.62 BSC		
М	0°	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

SO-20 **DW SUFFIX** CASE 751D-05 ISSUE F



- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

- MAXIMUM MOLD FRO HOSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION SHALL
 BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27	BSC	
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0 °	7 °	



Notes

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